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SEMICONDUCTOR®

FGA180N33AT 330V, 180A PDP Trench IGBT

Features

- High Current Capability
- Low saturation voltage: V_{CE(sat)} =1.03V @ I_C = 40A
- High input impedance
- · RoHS compliant

Applications

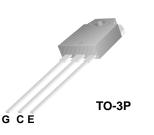
PDP SYSTEM

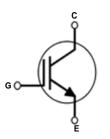


General Description

Using Novel Trench IGBT Technology, Fairchild's new series of trench IGBTs offer the optimum performance for PDP applications where low conduction and switching losses are essential.

April 2008





Absolute Maximum Ratings

Symbol	Description		Ratings	Units
V _{CES}	Collector to Emitter Voltage		330	V
V _{GES}	Gate to Emitter Voltage		± 30	V
I _C	Collector Current	@ T _C = 25 ^o C	180	A
I _{C pulse (1)}	Pulsed Collector Current	@ T _C = 25°C	450	А
P _D	Maximum Power Dissipation	@ T _C = 25 ^o C	390	W
	Maximum Power Dissipation	@ T _C = 100°C	156	W
TJ	Operating Junction Temperature		-55 to +150	°C
T _{stg}	Storage Temperature Range		-55 to +150	°C
TL	Maximum Lead Temp. for soldering Purposes, 1/8" from case for 5 seconds		300	°C

Notes:

1: Repetitive test, pulse width = 100usec, Duty = 0.1

* I_{C_}pulse limited by max Tj

Thermal Characteristics

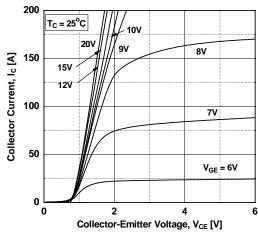
Symbol	Parameter	Тур.	Max.	Units
$R_{\theta JC}$ (IGBT)	Thermal Resistance, Junction to Case	-	0.32	°C/W
$R_{ ext{ heta}JA}$	Thermal Resistance, Junction to Ambient	-	40	°C/W

				Packaging				Qty per
Device Marking		Device	Package	Туре	Qty pe	er Tube	Box	
FGA180N33AT FGA180N33ATTU		TO-3P	TO-3P Tube		30ea		-	
Electric	al Cha	racteristics of th	ne IGBT T _{c = 2}	5°C unless otherwise noted				
Symbol		Parameter	Test	Conditions	Min.	Тур.	Max.	Units
Off Charac	teristics							
BV _{CES}	Collector	to Emitter Breakdown Vo	Itage V _{GE} = 0V, I _C	e = 250μA	330	-	-	V
ICES		Cut-Off Current	V _{CE} = V _{CES}		-	-	250	μA
I _{GES}	G-E Leak	age Current	V _{GE} = V _{GES}		-	-	±400	nA
On Charac	toristics					1		1
V _{GE(th)}		G-E Threshold Voltage		$I_{\rm C}$ = 250uA, $V_{\rm CE}$ = $V_{\rm GE}$		4.0	5.5	V
	Collector to Emitter Saturation Voltage		I _C = 40A, V _G		-	1.1	1.4	V
			I _C = 180A, V	_{GE} = 15V,	-	1.68	-	V
			I _C = 180A, V T _C = 125°C	_{GE} = 15V	-	1.89	_	V
Dynamic C	haractoris	tion						1
C _{ies}	Input Cap			V _{CE} = 30V, V _{GE} = 0V, f = 1MHz		3880	-	pF
C _{oes}	Output Ca	apacitance				305	-	pF
C _{res}	Reverse	Transfer Capacitance	f = 1MHz			180	-	pF
	Character							I
Switching t _{d(on)}		Delay Time			-	27	-	ns
t _r	Rise Time		$V_{\rm CC} = 200 V_{\rm cc}$	I _C = 40A,	-	80	-	ns
t _{d(off)}	Turn-Off I	Delay Time	$R_G = 5\Omega, V_G$	_{GE} = 15V, ad, T _C = 25 ^o C	-	108	-	ns
t _f	Fall Time			uu, 10 - 20 0	-	180	240	ns
t _{d(on)}	Turn-On I	Delay Time			-	26	-	ns
t _r	Rise Time	9	$V_{\rm CC} = 200V_{\rm CC}$	$I_{\rm C} = 40$ A,	-	75	-	ns
t _{d(off)}	Turn-Off I	Delay Time	R _G = 5Ω, V _G Resistive Lo	_{GE} = 15V, ad, T _C = 125°C	-	112	-	ns
t _f	Fall Time			J	-	250	300	ns
Qg	Total Gate	e Charge			-	169	-	nC
Q _{ge}	Gate to E	mitter Charge	$V_{CE} = 200V,$	I _C = 40A,	-	22	-	nC
Q _{gc}	Gate to C	ollector Charge	vGE = 15V	V _{GE} = 15V		69	-	nC

FGA180N33AT 330V, 180A PDP Trench IGBT

Typical Performance Characteristics

Figure 1. Typical Output Characteristics





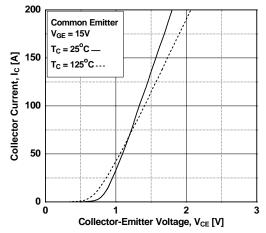


Figure 5. Saturation Voltage vs. Case Temperature at Variant Current Level

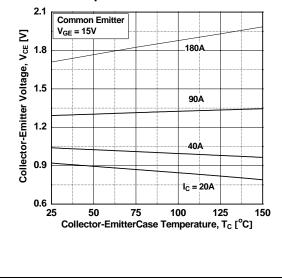


Figure 2. Typical Output Characteristics

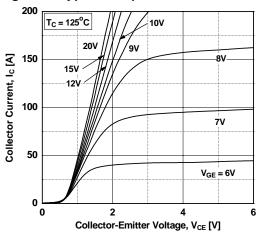


Figure 4. Transfer Characteristics

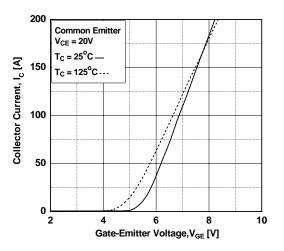
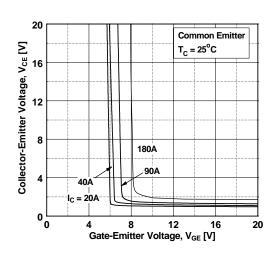


Figure 6. Saturation Voltage vs. V_{GE}



FGA180N33AT 330V, 180A PDP Trench IGBT

Typical Performance Characteristics

Figure 7. Saturation Voltage vs. V_{GE}

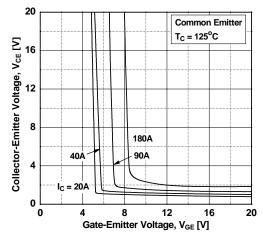


Figure 9. Gate charge Characteristics

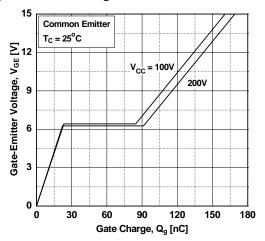
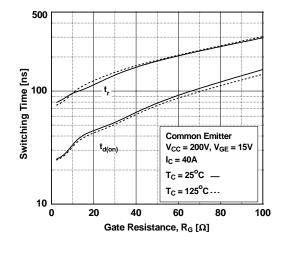
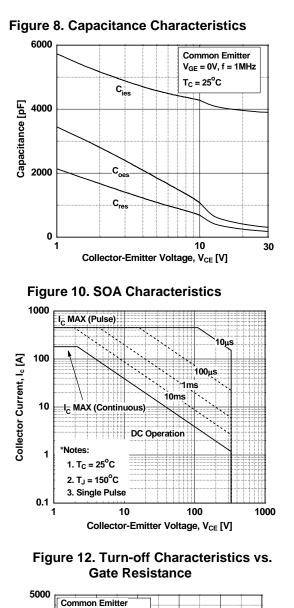
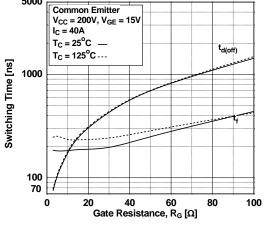


Figure 11. Turn-on Characteristics vs. Gate Resistance







FGA180N33AT Rev. A

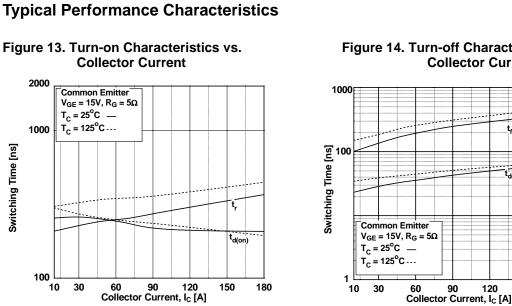
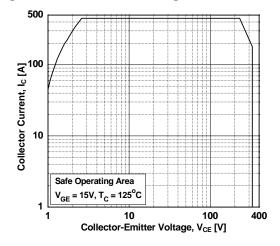
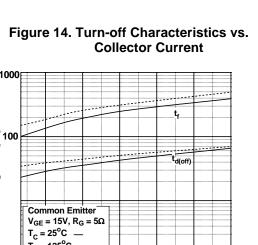


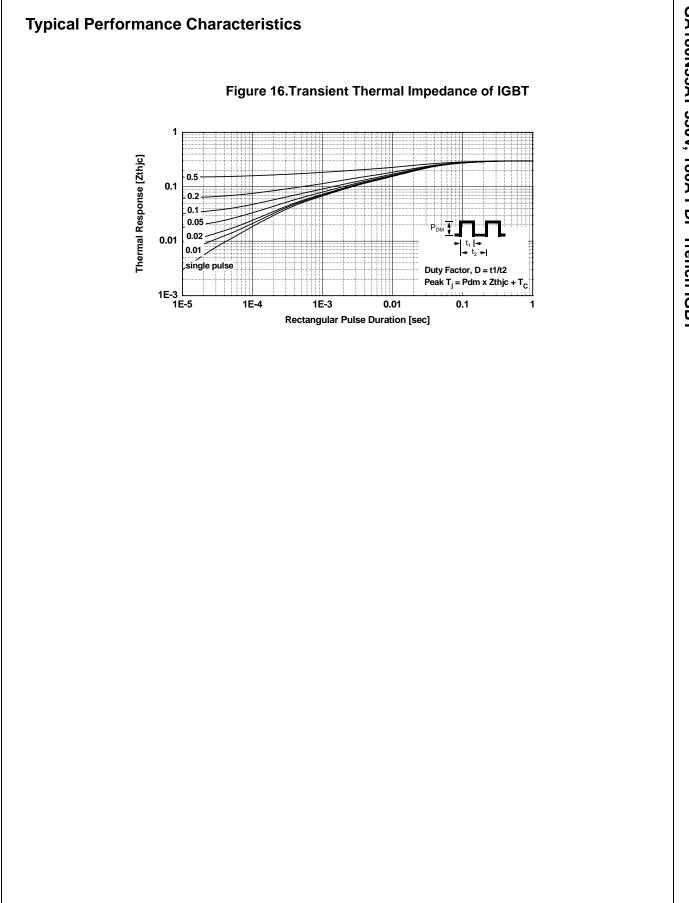
Figure 15. Turn off Switching SOA Characteristics

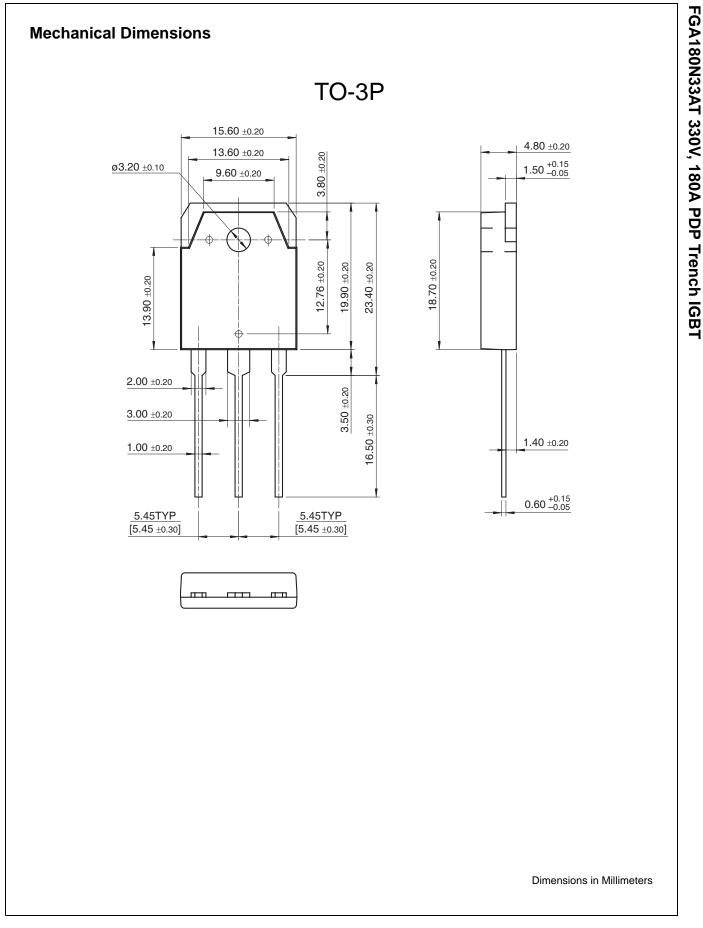




150

180





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